

MAPbI₃ deposition by LV-PSE on TiO₂ for photovoltaic application

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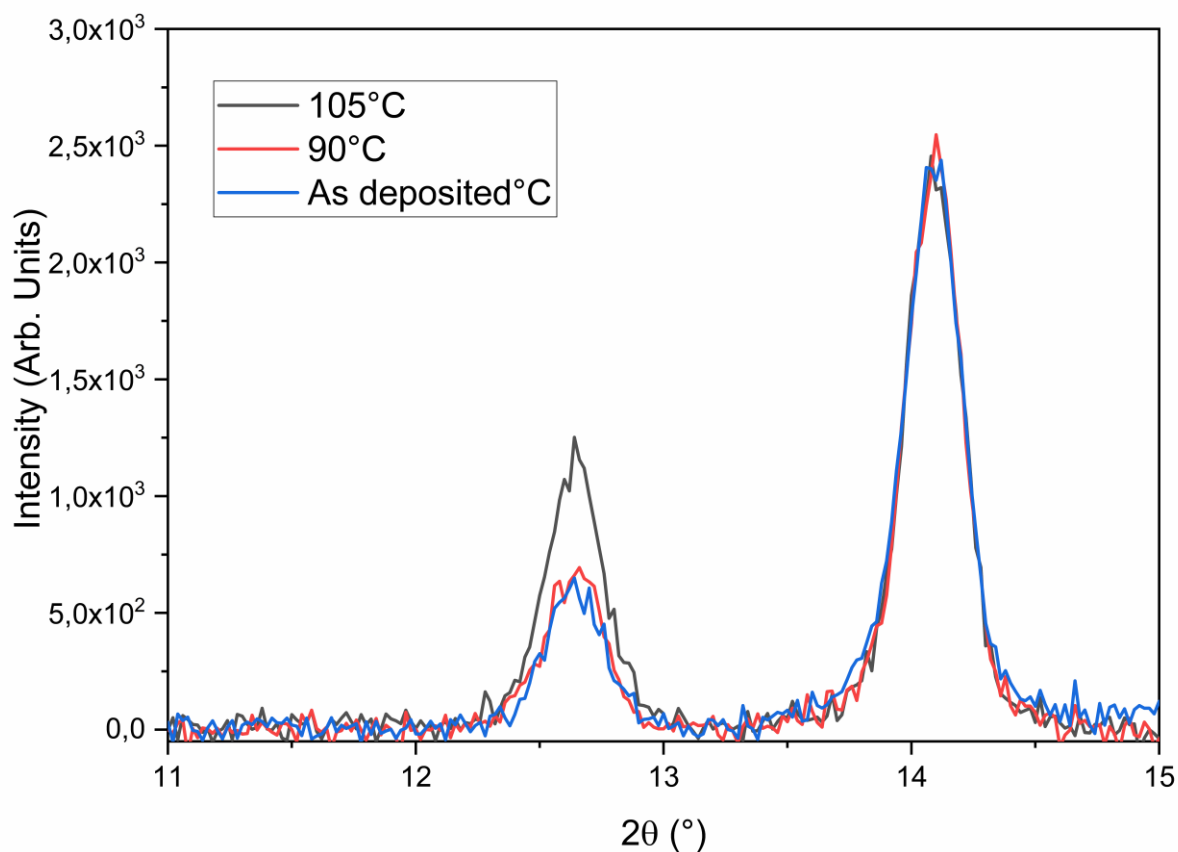


Figure S 1 XRD collected on as deposited MAPbI₃ (black line), MAPbI₃ annealed at 90°C for 1 hour (red line) and MAPbI₃ annealed at 105°C for 1 hour (blue line). All annealing processes were performed under dry N₂ environment.

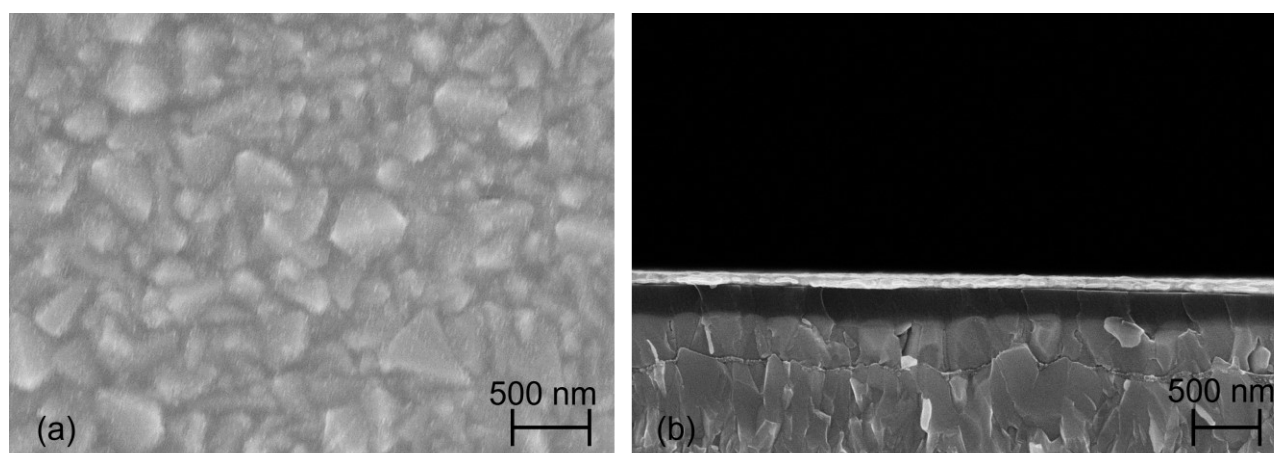


Figure S 2 (a) Top-view SEM image of the FTO/TiO₂ substrate: the morphology is mostly due to the FTO roughness, being the TiO₂ film very thin. (b) Cross section of the Low-magnification SEM image of the FTO/TiO₂/MAPbI₃ stack.